# 2<sup>nd</sup>Generation thinQ!<sup>™</sup> SiC Schottky Diode

# Features

- Revolutionary semiconductor material Silicon Carbide
- Switching behavior benchmark
- No reverse recovery/ No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 5mA<sup>2)</sup>

# thinQ! 2G Diode specially designed for fast switching applications like:

- CCM PFC
- Motor Drives

Туре	Package	Marking	Pin 1	Pin 2
IDH04S60C	PG-TO220-2	D04S60C	С	А

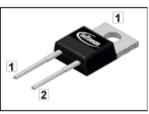
**Maximum ratings,** at  $T_i=25$  °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	I <sub>F</sub>	<i>T</i> <sub>C</sub> <140 °C	4	А
RMS forward current	I <sub>F,RMS</sub>	f=50 Hz	5.6	
reasonably be expected to cause the failure of that life-support , automotive, aviation and	I <sub>F,SM</sub>	T <sub>C</sub> =25 °C, <i>t</i> <sub>p</sub> =10 ms	32	
Life support systems are intended to b	I <sub>F,RM</sub>	T <sub>j</sub> =150 °C, T <sub>C</sub> =100 °C, <i>D</i> =0.1	18	
and sustain and/or protect human life.	I <sub>F,max</sub>	<i>T</i> <sub>C</sub> =25 °C, <i>t</i> <sub>p</sub> =10 μs	132	
of the user or other persons may be e	V <sub>RRM</sub>		600	V
Diode dv/dt ruggedness	dv∕dt	V <sub>R</sub> = 0480V	50	V/ns
Power dissipation	P <sub>tot</sub>	7 <sub>с</sub> =25 °С	42	W
Operating and storage temperature	T <sub>j</sub> , T <sub>stg</sub>		-55 175	°C
Mounting torque		M3 and M3.5 screws	60	Mcm
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	1.6mm (0.063 in.) from case for 10s	260	°C

# **Product Summary**

V <sub>DC</sub>	600	V
Q <sub>c</sub>	8	nC
I <sub>F</sub>	4	A









min typ max	Parameter	Symbol	Conditions		Values		Unit
				min.	typ.	max.	

### **Thermal characteristics**

Thermal resistance, junction - case	$R_{\mathrm{thJC}}$		-	-	3.6	K/W
Thermal resistance, junction - ambient	$R_{\mathrm{thJA}}$	leaded	-	-	62	

**Electrical characteristics,** at  $T_j$ =25 °C, unless otherwise specified

### Static characteristics

DC blocking voltage	V <sub>DC</sub>	/ <sub>R</sub> =0.05 mA	600	-	-	V
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> =4 A, <i>T</i> <sub>j</sub> =25 °C	-	1.7	1.9	
		I <sub>F</sub> =4 A, <i>T</i> <sub>j</sub> =150 °C	-	2	2.4	
Reverse current	I <sub>R</sub>	V <sub>R</sub> =600 V, <i>T</i> <sub>j</sub> =25 °C	-	0.5	50	μA
		V <sub>R</sub> =600 V, <i>T</i> <sub>j</sub> =150 °C	-	2	500	

### Infineon Technologies components may be used in life-support devices or systems

### and/or automotive, aviation and aerospace applications or systems only with

reasonably be expected to cause the f Q	c	V <sub>R</sub> =400 V,/ <sub>F</sub> ≤/ <sub>F.max</sub> ,	-	8	-	nC
aerospace device or system or to affect t		d <i>i<sub>F</sub></i> /d <i>t</i> =200 A/µs,				
Life support systems are intended to $b t_c$	;	T <sub>j</sub> =150 °C	-	-	<10	ns
and sustain and/or protect human life. C	;	$V_{R}$ =1 V, $f$ = MHz	-	130	-	pF
of the user or other persons may be endangered.		V <sub>R</sub> =600 V, <i>f</i> =1 MHz	-	20	-	

### <sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> All devices tested under avalanche conditions, for a time periode of 5ms, at 5mA.

 $^{3)}t_{c}$  is the time constant for the capacitive displacement current waveform (independent from T<sub>j</sub>, I<sub>LOAD</sub> and di/dt), different from t<sub>rr</sub>, which is dependent on T<sub>j</sub>, I<sub>LOAD</sub>, di/dt. No reverse recovery time constant t<sub>rr</sub> due to absence of minority carrier injection.

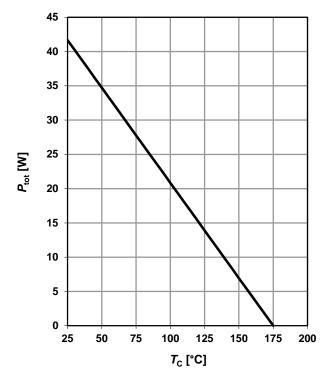
<sup>4)</sup> Only capacitive charge occuring, guaranteed by design.



### **1** Power dissipation

 $P_{tot}=f(T_C)$ 

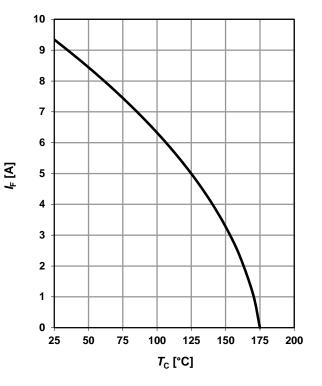
parameter: R<sub>thJC(max)</sub>



# 2 Diode forward current

 $I_{\rm F}=f(T_{\rm C}); T_{\rm j} \le 175 \ ^{\circ}{\rm C}$ 

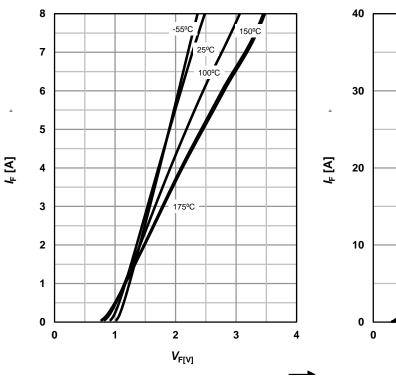
parameter: R<sub>thJC(max)</sub>; V<sub>F(max)</sub>



# 3 Typ. forward characteristic

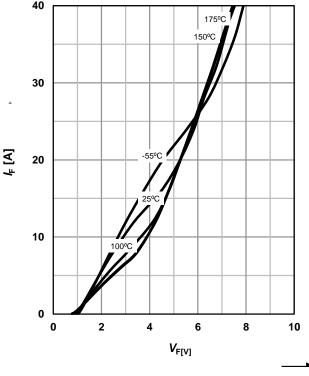
 $I_{\rm F}$ =f( $V_{\rm F}$ );  $t_{\rm p}$ =400 µs

parameter: T<sub>j</sub>



# 4 Typ. forward characteristic in surge current mode

 $I_{\rm F}$ =f( $V_{\rm F}$ );  $t_{\rm p}$ =400 µs; parameter: T<sub>j</sub>

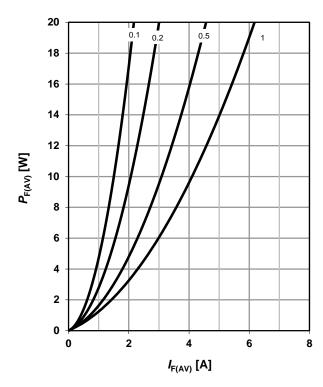




### 5 Typ. forward power dissipation vs.

### average forward current

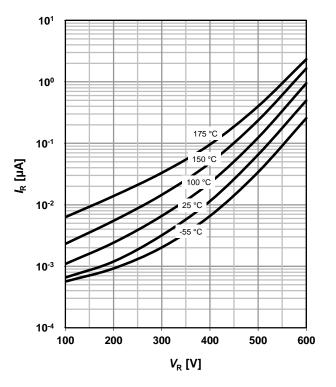
 $P_{F,AV}=f(I_F)$ ,  $T_C=100$  °C, parameter:  $D=t_p/T$ 



## 6 Typ. reverse current vs. reverse voltage

 $I_{\rm R}=f(V_{\rm R})$ 

parameter:  $T_j$ 



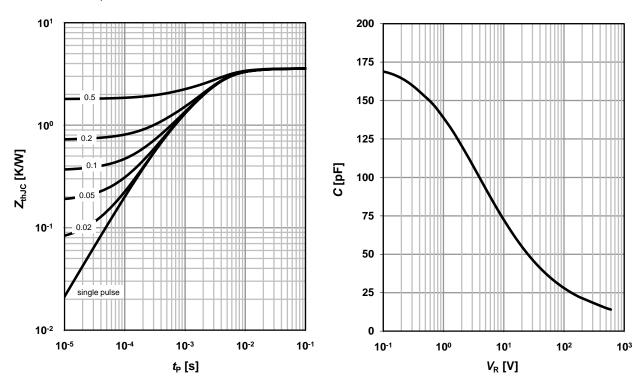
8 Typ. capacitance vs. reverse voltage

 $C=f(V_R)$ ;  $T_C=25$  °C, f=1 MHz

# 7 Transient thermal impedance

 $Z_{thJC}=f(t_p)$ 

parameter:  $D = t_p/T$ 



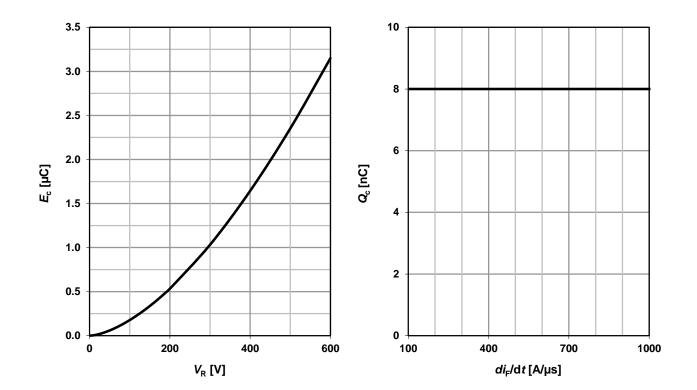


 $E_{\rm C}=f(V_{\rm R})$ 

### 9 Typ. C stored energy

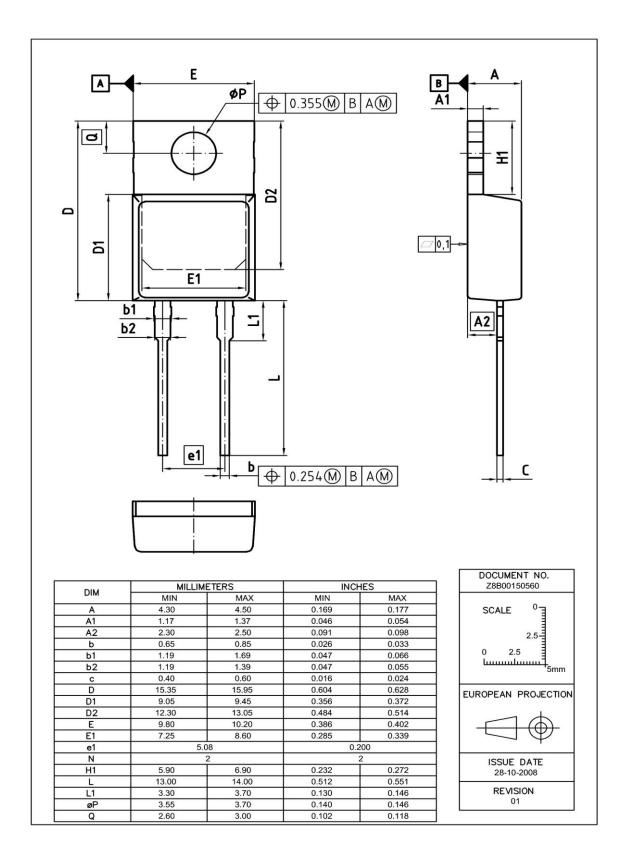
10 Typ. capacitance charge vs. current slope

 $Q_{C} = f(di_{F}/dt)^{4}; T_{j} = 150 \text{ °C}; I_{F} \leq I_{F,max}$ 





### PG-TO220-2: Outline



### Dimensions in mm/inches

IDH04S60C



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